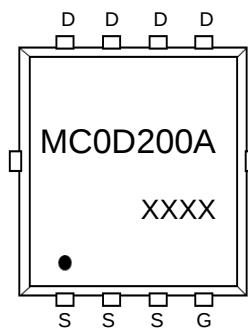


Features

- Trench Power LV MOSFET technology
- Excellent package for heat dissipation
- High density cell design for low $R_{DS(ON)}$

Application

- High current load applications
- Load switching
- Hard switched and high frequency circuits

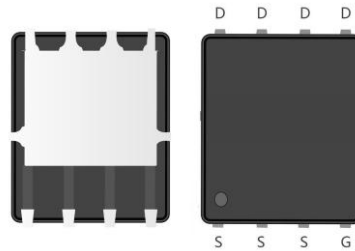


MC0D200A: Device code
XXXX : Code

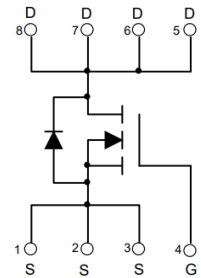
Marking and pin assignment

Product Summary

V_{DS}	$R_{DS(ON)}$ TYP	I_D
30V	1.6m Ω @10V	200A
	2.6m Ω @4.5V	



PDFN5X6-8L view



Schematic diagram

Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Symbol	Parameter	Rating	Unit
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Common Ratings (TC=25°C Unless Otherwise Noted)

V_{DS}	Drain-Source Breakdown Voltage	30	V
V_{GS}	Gate-Source Voltage	± 20	V
T_J	Maximum Junction Temperature	150	°C
T_{STG}	Storage Temperature Range	-50 to 155	°C
I_S	Diode Continuous Forward Current	$T_C=25^\circ\text{C}$ 200	A

Mounted on Large Heat Sink

I_{DM}	Pulse Drain Current Tested	$T_C=25^\circ\text{C}$ 700	A
I_D	Continuous Drain Current	$T_C=25^\circ\text{C}$ 200	A
P_D	Maximum Power Dissipation	$T_C=25^\circ\text{C}$ 69	W
E_{AS}	Single pulse avalanche energy ^{Note1}	46.5	mJ

Electrical Characteristics (T _J =25℃ unless otherwise noted)						
Symbol	Parameter	Condition	Min	Typ	Max	Unit
Static Electrical Characteristics @ T _J = 25℃ (unless otherwise stated)						
B _{V(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	30	--	--	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =30V, V _{GS} =0V	--	--	1.0	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} =±20V, V _{DS} =0V	--	--	±100	nA
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _D =250μA	1.0	1.5	2.5	V
R _{DS(on)}	Drain-Source On-State Resistance	V _{GS} =10V, I _D =20A	--	1.6	2	mΩ
		V _{GS} =4.5V, I _D =20A	--	2.6	3.3	mΩ
Dynamic Electrical Characteristics @ T _J = 25℃ (unless otherwise stated)						
C _{ISS}	Input Capacitance	V _{DS} =15V, V _{GS} =0V, f=1MHz	--	4498	--	pF
C _{OSS}	Output Capacitance		--	800	--	pF
C _{RSS}	Reverse Transfer Capacitance		--	643	--	pF
Switching Characteristics						
Q _g	Total Gate Charge	V _{DS} =15V, I _D =20A, V _{GS} =10V	--	92.7	--	nC
Q _{gs}	Gate Source Charge		--	13.5	--	nC
Q _{gd}	Gate Drain Charge		--	22.8	--	nC
t _{d(on)}	Turn-on Delay Time	V _{DD} =20V, R _L =0.75Ω, V _{GS} =10V, R _G =3Ω	--	11	--	nS
t _r	Turn-on Rise Time		--	80	--	nS
t _{d(off)}	Turn-Off Delay Time		--	39	--	nS
t _f	Turn-Off Fall Time		--	92	--	nS
Source- Drain Diode Characteristics						
V _{SD}	Forward on voltage	T _J =25℃, I _S =20A	--	--	1.2	V

Note :

1、EAS Test Condition: L=2.0mH, I_{AS}=20A, V_{DD}=30V, V_{GS}=10V, I_{AS}=20A, T_J=25°C

Typical Operating Characteristics

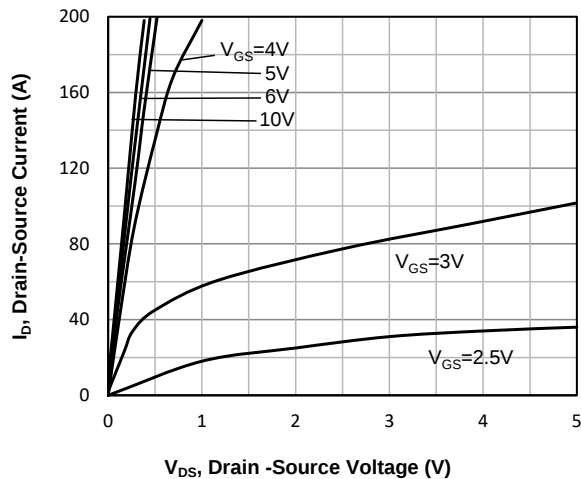


Fig1. Typical Output Characteristics

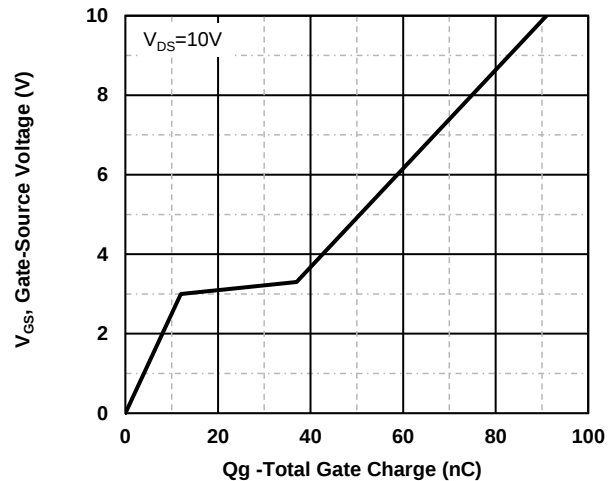


Fig2. Typical Gate Charge Vs. Gate-Source Voltage

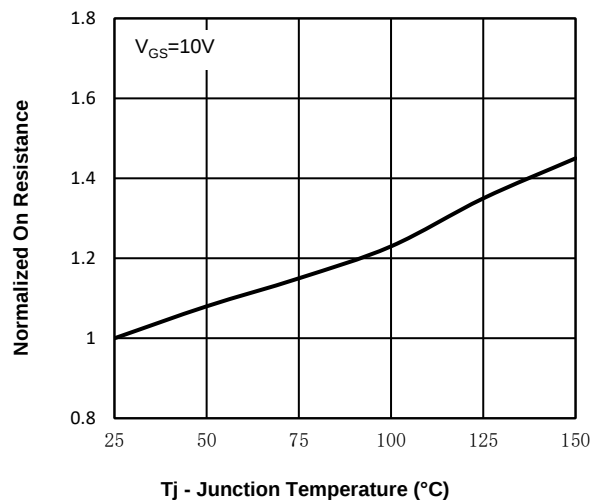


Fig3. Normalized On Resistance Vs. Temperature

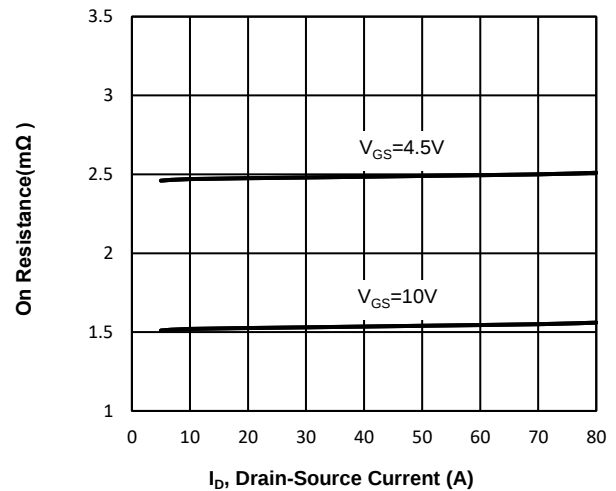


Fig4. On-Resistance Vs. Drain-Source Current

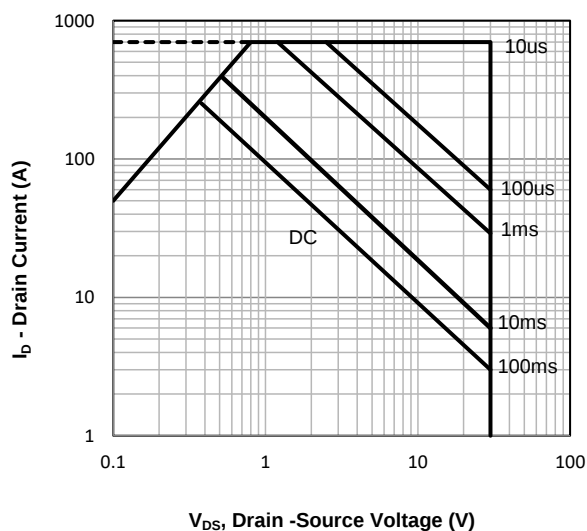


Fig5. Maximum Safe Operating Area

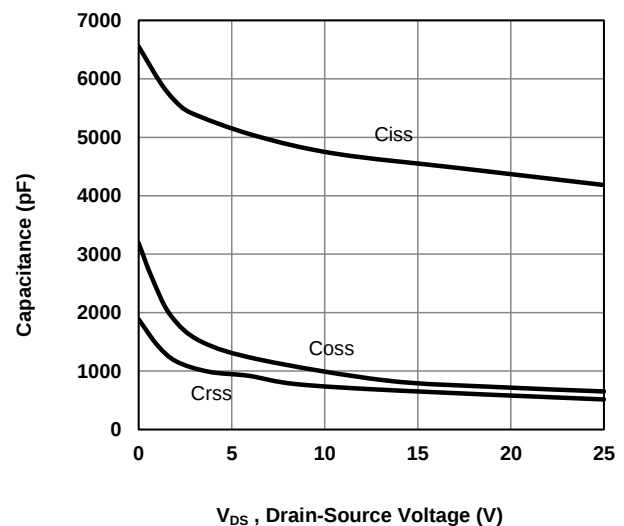
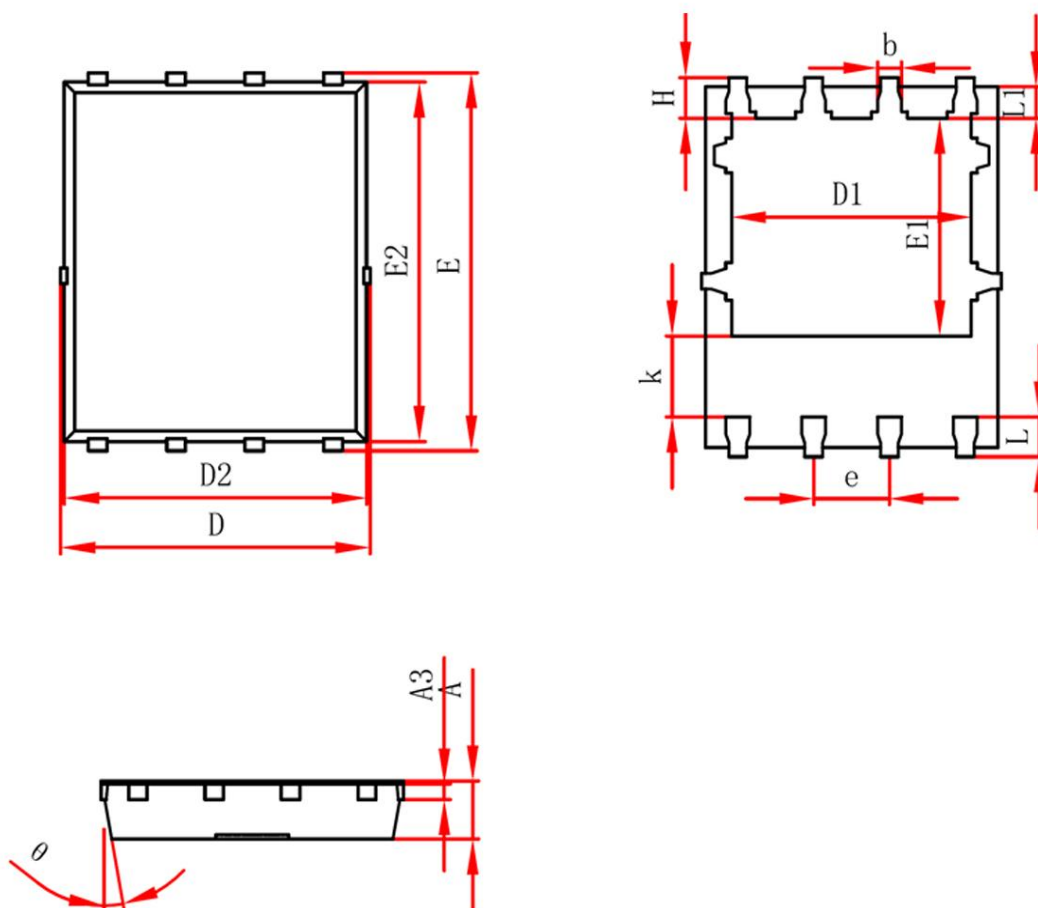


Fig6. Typical Capacitance Vs. Drain-Source Voltage

PDFN5X6-8L Package information


Symbol	Dimensions in Millimeters(mm)		Dimensions In Inches	
	Min	Max	Min	Max
A	0.950	1.050	0.035	0.039
A3	0.254REF.		0.010REF.	
D	4.950	5.050	0.196	0.200
E	5.950	6.050	0.235	0.239
D1	4.026	4.126	0.159	0.163
E1	3.510	3.610	0.139	0.143
D2	4.850	4.950	0.192	0.196
E2	5.700	5.800	0.225	0.229
k	1.190	1.390	0.047	0.055
b	0.300	0.400	0.012	0.016
e	1.270TYP.		0.050TYP.	
L	0.559	0.711	0.022	0.028
L1	0.424	0.576	0.017	0.023
H	0.574	0.726	0.023	0.029
θ	10°	12°	10°	12°